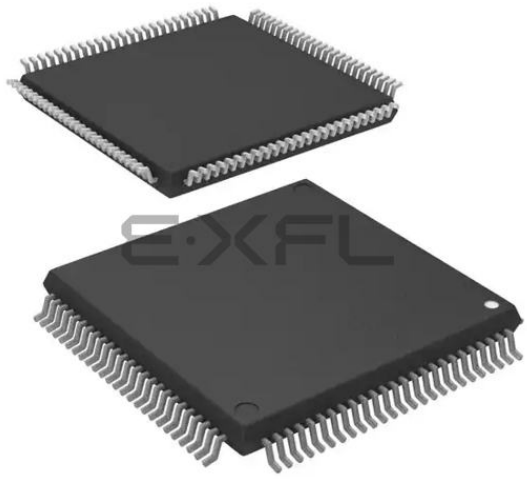
Renesas Electronics America Inc - M30624FGPGP#U3C Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	85
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30624fgpgp-u3c

1. Overview

The M16C/62P Group (M16C/62P, M16C/62PT) of single-chip microcomputers are built using the high performance silicon gate CMOS process using a M16C/60 Series CPU core and are packaged in a 80-pin, 100-pin and 128-pin plastic molded QFP. These single-chip microcomputers operate using sophisticated instructions featuring a high level of instruction efficiency. With 1M bytes of address space, they are capable of executing instructions at high speed. In addition, this microcomputer contains a multiplier and DMAC which combined with fast instruction processing capability, makes it suitable for control of various OA, communication, and industrial equipment which requires high-speed arithmetic/logic operations.

1.1 Applications

Audio, cameras, television, home appliance, office/communications/portable/industrial equipment, automobile, etc.

Specifications written in this manual are believed to be accurate, but are not guaranteed to be entirely free of error. Specifications in this manual may be changed for functional or performance improvements. Please make sure your manual is the latest edition.

Table 1.5 Product List (2) (M16C/62P) As of Dec. 2005

Type No.	ROM Capacity	RAM Capacity	Package Type (1)	Remarks
M30622MHP-XXXFP	384 Kbytes	16 Kbytes	PRQP0100JB-A	Mask ROM version
M30622MHP-XXXGP			PLQP0100KB-A	
M30623MHP-XXXGP			PLQP0128KB-A	
M30624MHP-XXXFP		24 Kbytes	PRQP0100JB-A	
M30624MHP-XXXGP			PLQP0100KB-A	
M30625MHP-XXXGP			PLQP0128KB-A	
M30626MHP-XXXFP		31 Kbytes	PRQP0100JB-A	
M30626MHP-XXXGP			PLQP0100KB-A	
M30627MHP-XXXGP			PLQP0128KB-A	
M30626MJP-XXXFP (D)	512 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626MJP-XXXGP (D)			PLQP0100KB-A	
M30627MJP-XXXGP (D)			PLQP0128KB-A	
M30622F8PFP	64K+4 Kbytes	4 Kbytes	PRQP0100JB-A	Flash memory version (2)
M30622F8PGP			PLQP0100KB-A	
M30623F8PGP			PRQP0080JA-A	
M30620FCPFP	128K+4 Kbytes	10 Kbytes	PRQP0100JB-A	
M30620FCPGP			PLQP0100KB-A	
M30621FCPGP			PRQP0080JA-A	
M3062LFGPFP(3) (D)	256K+4 Kbytes	20 Kbytes	PRQP0100JB-A	
M3062LFGPGP(3) (D)			PLQP0100KB-A	
M30625FGPGP			PLQP0128KB-A	
M30626FHPFP	384K+4 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626FHPGP			PLQP0100KB-A	
M30627FHPGP			PLQP0128KB-A	
M30626FJPFP	512K+4 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626FJPGP			PLQP0100KB-A	
M30627FJPGP			PLQP0128KB-A	
M30622SPFP	–	4 Kbytes	PRQP0100JB-A	ROM-less version
M30622SPGP			PLQP0100KB-A	
M30620SPFP		10 Kbytes	PRQP0100JB-A	
M30620SPGP			PLQP0100KB-A	
M30624SPFP (D)	–	20 Kbytes	PRQP0100JB-A	
M30624SPGP (D)			PLQP0100KB-A	
M30626SPFP (D)		31 Kbytes	PRQP0100JB-A	
M30626SPGP (D)			PLQP0100KB-A	

(D): Under development

NOTES:

1. The old package type numbers of each package type are as follows.
   PLQP0128KB-A : 128P6Q-A,
   PRQP0100JB-A : 100P6S-A,
   PLQP0100KB-A : 100P6Q-A,
   PRQP0080JA-A : 80P6S-A
2. In the flash memory version, there is 4K bytes area (block A).
3. Please use M3062LFGPFP and M3062LFGPGP for your new system instead of M30624FGPFP and M30624FGPGP. The M16C/62P Group (M16C/62P, M16C/62PT) hardware manual is still good for M30624FGPFP and M30624FGPGP.

M30624FGPFP	256K+4 Kbytes	20 Kbytes	PRQP0100JB-A	Flash memory version
M30624FGPGP			PLQP0100KB-A	

Table 1.8 Product Code of Flash Memory version and ROMless version for M16C/62P

	Product Code	Package	Internal ROM (User ROM Area Without Block A, Block 1)		Internal ROM (Block A, Block 1)		Operating Ambient Temperature
			Program and Erase Endurance	Temperature Range	Program and Erase Endurance	Temperature Range	
Flash memory Version	D3	Lead-included	100	0°C to 60°C	100	0°C to 60°C	-40°C to 85°C
	D5						-20°C to 85°C
	D7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	D9					-20°C to 85°C	-20°C to 85°C
	U3	Lead-free	100		100	0°C to 60°C	-40°C to 85°C
	U5						-20°C to 85°C
	U7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	U9					-20°C to 85°C	-20°C to 85°C
ROM-less version	D3	Lead-included	–	–	–	–	-40°C to 85°C
	D5						-20°C to 85°C
	U3	Lead-free	–	–	–	–	-40°C to 85°C
	U5						-20°C to 85°C

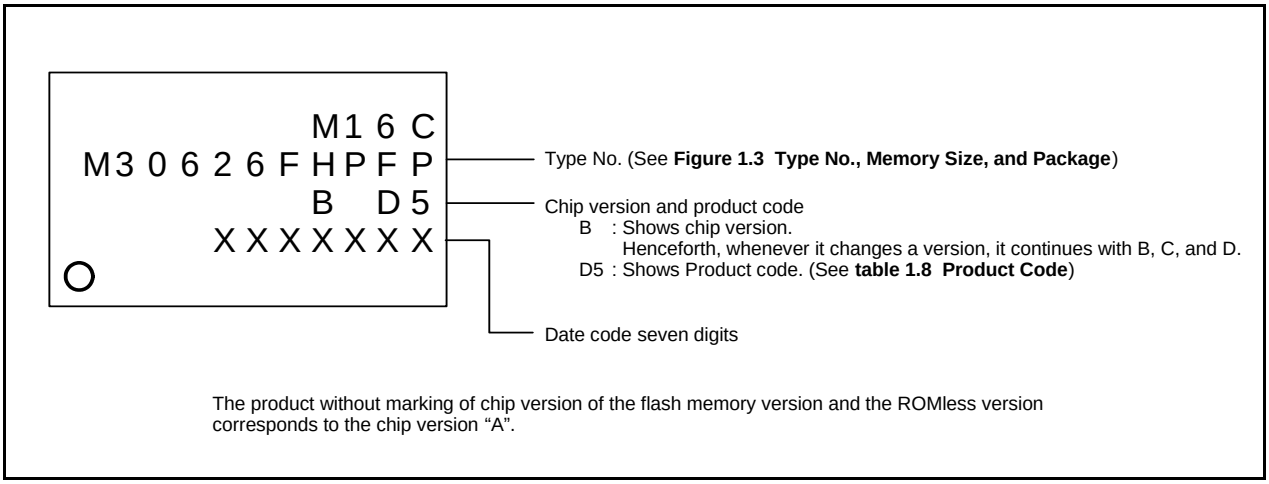


Figure 1.4 Marking Diagram of Flash Memory version and ROM-less version for M16C/62P (Top View)

Table 1.19 Pin Description (100-pin and 128-pin Version) (3)

Signal Name	Pin Name	I/O Type	Power Supply(1)	Description
Reference voltage input	VREF	I	VCC1	Applies the reference voltage for the A/D converter and D/A converter.
A/D converter	AN0 to AN7, AN0_0 to AN0_7, AN2_0 to AN2_7	I	VCC1	Analog input pins for the A/D converter.
	$\overline{\text{ADTRG}}$	I	VCC1	This is an A/D trigger input pin.
	ANEX0	I/O	VCC1	This is the extended analog input pin for the A/D converter, and is the output in external op-amp connection mode.
	ANEX1	I	VCC1	This is the extended analog input pin for the A/D converter.
D/A converter	DA0, DA1	O	VCC1	This is the output pin for the D/A converter.
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7 (2), P13_0 to P13_7 (2)	I/O	VCC2	8-bit I/O ports in CMOS, having a direction register to select an input or output. Each pin is set as an input port or output port. An input port can be set for a pull-up or for no pull-up in 4-bit unit by program.
	P6_0 to P6_7, P7_0 to P7_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7 (2)	I/O	VCC1	8-bit I/O ports having equivalent functions to P0. (however, output of P7_0 and P7_1 for the N-channel open drain output.)
	P8_0 to P8_4, P8_6, P8_7, P14_0, P14_1(2)	I/O	VCC1	I/O ports having equivalent functions to P0.
Input port	P8_5	I	VCC1	Input pin for the $\overline{\text{NMI}}$ interrupt. Pin states can be read by the P8_5 bit in the P8 register.

I : Input O : Output I/O : Input and output

NOTES:
1. When use VCC1 > VCC2, contacts due to some points or restrictions to be checked.
2. Ports P11 to P14 in M16C/62P (100-pin version) and M16C/62PT (100-pin version) cannot be used.

Table 4.2 SFR Information (2) (1)

Address	Register	Symbol	After Reset
0040h			
0041h			
0042h			
0043h			
0044h	INT3 Interrupt Control Register	INT3IC	XX00X000b
0045h	Timer B5 Interrupt Control Register	TB5IC	XXXXX000b
0046h	Timer B4 Interrupt Control Register, UART1 BUS Collision Detection Interrupt Control Register	TB4IC, U1BCNIC	XXXXX000b
0047h	Timer B3 Interrupt Control Register, UART0 BUS Collision Detection Interrupt Control Register	TB3IC, U0BCNIC	XXXXX000b
0048h	SI/O4 Interrupt Control Register, INT5 Interrupt Control Register	S4IC, INT5IC	XX00X000b
0049h	SI/O3 Interrupt Control Register, INT4 Interrupt Control Register	S3IC, INT4IC	XX00X000b
004Ah	UART2 Bus Collision Detection Interrupt Control Register	BCNIC	XXXXX000b
004Bh	DMA0 Interrupt Control Register	DM0IC	XXXXX000b
004Ch	DMA1 Interrupt Control Register	DM1IC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
0050h	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	Timer A0 Interrupt Control Register	TA0IC	XXXXX000b
0056h	Timer A1 Interrupt Control Register	TA1IC	XXXXX000b
0057h	Timer A2 Interrupt Control Register	TA2IC	XXXXX000b
0058h	Timer A3 Interrupt Control Register	TA3IC	XXXXX000b
0059h	Timer A4 Interrupt Control Register	TA4IC	XXXXX000b
005Ah	Timer B0 Interrupt Control Register	TB0IC	XXXXX000b
005Bh	Timer B1 Interrupt Control Register	TB1IC	XXXXX000b
005Ch	Timer B2 Interrupt Control Register	TB2IC	XXXXX000b
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Fh	INT2 Interrupt Control Register	INT2IC	XX00X000b
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

NOTES:
1. The blank areas are reserved and cannot be accessed by users.

X : Nothing is mapped to this bit

Table 4.6 SFR Information (6) (1)

Address	Register	Symbol	After Reset
03C0h 03C1h	A/D Register 0	AD0	XXh XXh
03C2h 03C3h	A/D Register 1	AD1	XXh XXh
03C4h 03C5h	A/D Register 2	AD2	XXh XXh
03C6h 03C7h	A/D Register 3	AD3	XXh XXh
03C8h 03C9h	A/D Register 4	AD4	XXh XXh
03CAh 03CBh	A/D Register 5	AD5	XXh XXh
03CCh 03CDh	A/D Register 6	AD6	XXh XXh
03CEh 03CFh	A/D Register 7	AD7	XXh XXh
03D0h			
03D1h			
03D2h			
03D3h			
03D4h	A/D Control Register 2	ADCON2	00h
03D5h			
03D6h	A/D Control Register 0	ADCON0	00000XXXb
03D7h	A/D Control Register 1	ADCON1	00h
03D8h	D/A Register 0	DA0	00h
03D9h			
03DAh	D/A Register 1	DA1	00h
03DBh			
03DCh	D/A Control Register	DACON	00h
03DDh			
03DEh	Port P14 Control Register (3)	PC14	XX00XXXXb
03DFh	Pull-Up Control Register 3 (3)	PUR3	00h
03E0h	Port P0 Register	P0	XXh
03E1h	Port P1 Register	P1	XXh
03E2h	Port P0 Direction Register	PD0	00h
03E3h	Port P1 Direction Register	PD1	00h
03E4h	Port P2 Register	P2	XXh
03E5h	Port P3 Register	P3	XXh
03E6h	Port P2 Direction Register	PD2	00h
03E7h	Port P3 Direction Register	PD3	00h
03E8h	Port P4 Register	P4	XXh
03E9h	Port P5 Register	P5	XXh
03EAh	Port P4 Direction Register	PD4	00h
03EBh	Port P5 Direction Register	PD5	00h
03ECh	Port P6 Register	P6	XXh
03EDh	Port P7 Register	P7	XXh
03EEh	Port P6 Direction Register	PD6	00h
03EFh	Port P7 Direction Register	PD7	00h
03F0h	Port P8 Register	P8	XXh
03F1h	Port P9 Register	P9	XXh
03F2h	Port P8 Direction Register	PD8	00X00000b
03F3h	Port P9 Direction Register	PD9	00h
03F4h	Port P10 Register	P10	XXh
03F5h	Port P11 Register (3)	P11	XXh
03F6h	Port P10 Direction Register	PD10	00h
03F7h	Port P11 Direction Register (3)	PD11	00h
03F8h	Port P12 Register (3)	P12	XXh
03F9h	Port P13 Register (3)	P13	XXh
03FAh	Port P12 Direction Register (3)	PD12	00h
03FBh	Port P13 Direction Register (3)	PD13	00h
03FCh	Pull-Up Control Register 0	PUR0	00h
03FDh	Pull-Up Control Register 1	PUR1	00000000b (2) 00000010b (2)
03FEh	Pull-Up Control Register 2	PUR2	00h
03FFh	Port Control Register	PCR	00h

NOTES:
1. The blank areas are reserved and cannot be accessed by users.
2. At hardware reset 1 or hardware reset 2, the register is as follows:
   - "00000000b" where "L" is inputted to the CNVSS pin
   - "00000010b" where "H" is inputted to the CNVSS pin

   At software reset, watchdog timer reset and oscillation stop detection reset, the register is as follows:
   - "00000000b" where the PM01 to PM00 bits in the PM0 register are "00b" (single-chip mode).
   - "00000010b" where the PM01 to PM00 bits in the PM0 register are "01b" (memory expansion mode) or "11b" (microprocessor mode).
3. These registers do not exist in M16C/62P (80-pin version), and M16C/62PT (80-pin version).

X : Nothing is mapped to this bit

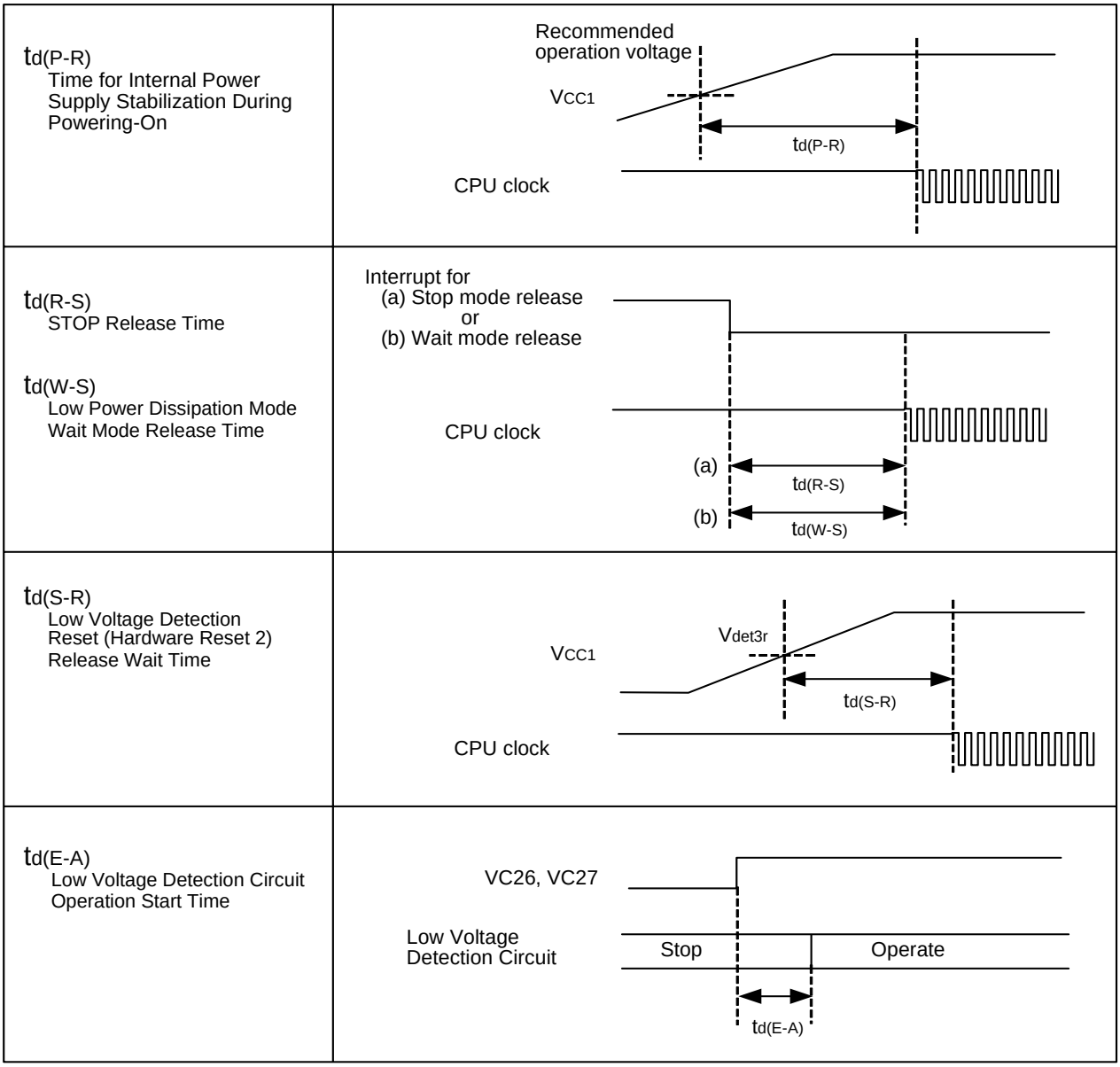


Figure 5.1 Power Supply Circuit Timing Diagram

Table 5.12 Electrical Characteristics (2) (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
I_{CC}	Power Supply Current (V_{CC1}=V_{CC2}=4.0V to 5.5V)	In single-chip mode, the output pins are open and other pins are V_{SS}	Mask ROM	f(BCLK)=24MHz No division, PLL operation		14	20	mA
				No division, On-chip oscillation		1		mA
			Flash Memory	f(BCLK)=24MHz, No division, PLL operation		18	27	mA
				No division, On-chip oscillation		1.8		mA
			Flash Memory Program	f(BCLK)=10MHz, VCC1=5.0V		15		mA
			Flash Memory Erase	f(BCLK)=10MHz, VCC1=5.0V		25		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM (3)		25		µA
			Flash Memory	f(BCLK)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(BCLK)=32kHz Low power dissipation mode, Flash Memory (3)		420		µA
				On-chip oscillation, Wait mode		50		µA
			Mask ROM Flash Memory	f(BCLK)=32kHz Wait mode (2), Oscillation capability High		7.5		µA
				f(BCLK)=32kHz Wait mode (2), Oscillation capability Low		2.0		µA
				Stop mode Topr =25°C		0.8	3.0	µA
I_{det4}	Low Voltage Detection Dissipation Current (4)					0.7	4	µA
I_{det3}	Reset Area Detection Dissipation Current (4)					1.2	8	µA

NOTES:
1. Referenced to V_{CC1}=V_{CC2}=4.2 to 5.5V, V_{SS} = 0V at T_{opr} = –20 to 85°C / –40 to 85°C, f(BCLK)=24MHz unless otherwise specified.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.
4. I_{det} is dissipation current when the following bit is set to “1” (detection circuit enabled).

   I_{det4}: VC27 bit in the VCR2 register

   I_{det3}: VC26 bit in the VCR2 register

$V_{CC1}=V_{CC2}=5V$

Timing Requirements
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.21 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on one edge)	100		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on one edge)	40		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on one edge)	40		ns
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on both edges)	200		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on both edges)	80		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on both edges)	80		ns

Table 5.22 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.23 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.24 A/D Trigger Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(AD)}$	$\overline{\text{ADTRG}}$ Input Cycle Time	1000		ns
$t_{w(ADL)}$	$\overline{\text{ADTRG}}$ input LOW Pulse Width	125		ns

Table 5.25 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi Input Cycle Time	200		ns
$t_{w(CKH)}$	CLKi Input HIGH Pulse Width	100		ns
$t_{w(CKL)}$	CLKi Input LOW Pulse Width	100		ns
$t_{d(C-Q)}$	TXDi Output Delay Time		80	ns
$t_{h(C-Q)}$	TXDi Hold Time	0		ns
$t_{su(D-C)}$	RXDi Input Setup Time	70		ns
$t_{h(C-D)}$	RXDi Input Hold Time	90		ns

Table 5.26 External Interrupt $\overline{\text{INTi}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{\text{INTi}}$ Input HIGH Pulse Width	250		ns
$t_{w(INL)}$	$\overline{\text{INTi}}$ Input LOW Pulse Width	250		ns

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.27 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.2**		25	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			25	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			15	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		–4		ns
td(BCLK-RD)	RD Signal Output Delay Time			25	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			25	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

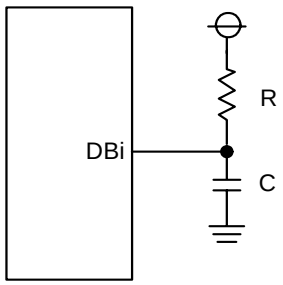
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns]$$ f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
   = 6.7ns.



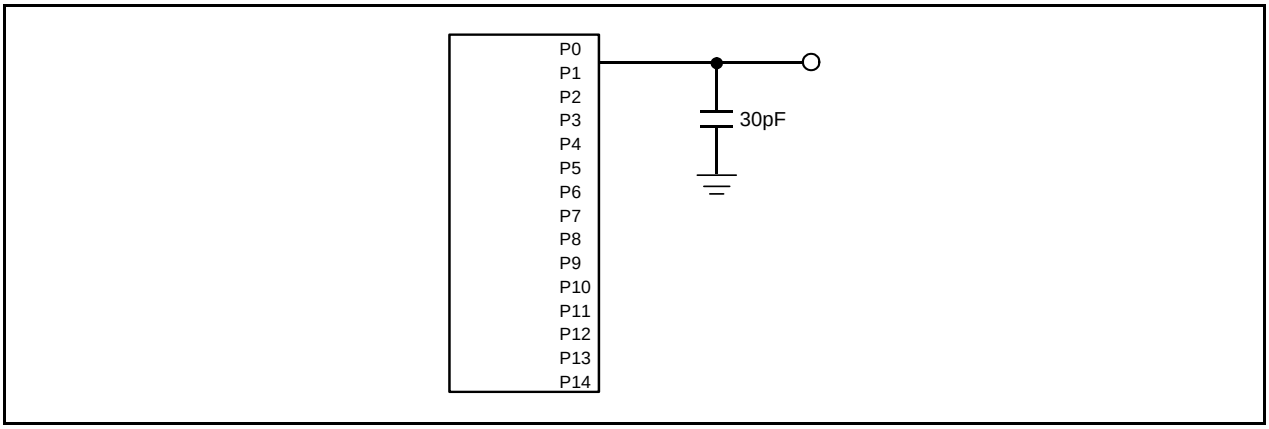


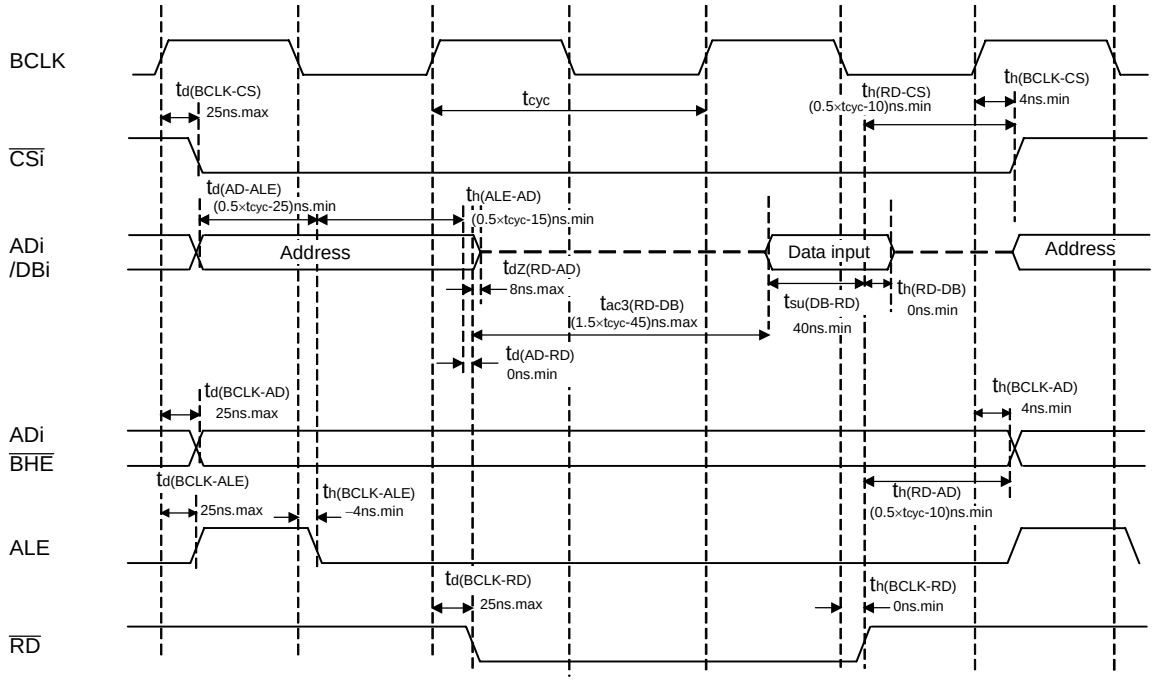
Figure 5.2 Ports P0 to P14 Measurement Circuit

$V_{CC1}=V_{CC2}=5V$

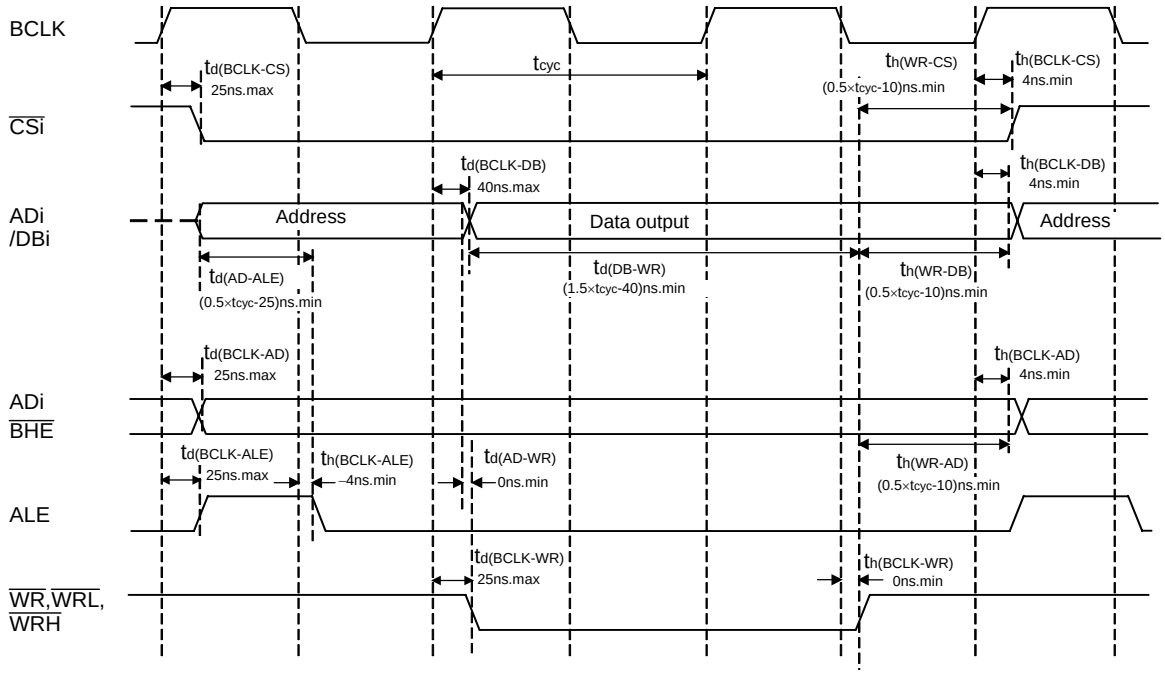
Memory Expansion Mode, Microprocessor Mode

(For 1- or 2-wait setting, external area access and multiplex bus selection**)**

Read timing



Write timing



Measuring conditions
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
· Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.10 Timing Diagram (8)

$V_{CC1}=V_{CC2}=3V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.46 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.12**		30	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			30	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			25	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		–4		ns
td(BCLK-RD)	RD Signal Output Delay Time			30	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			30	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

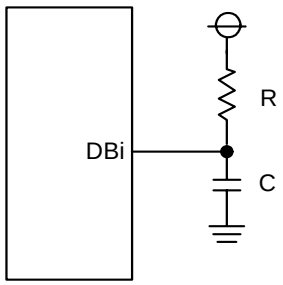
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns]$$ f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
   = 6.7ns.



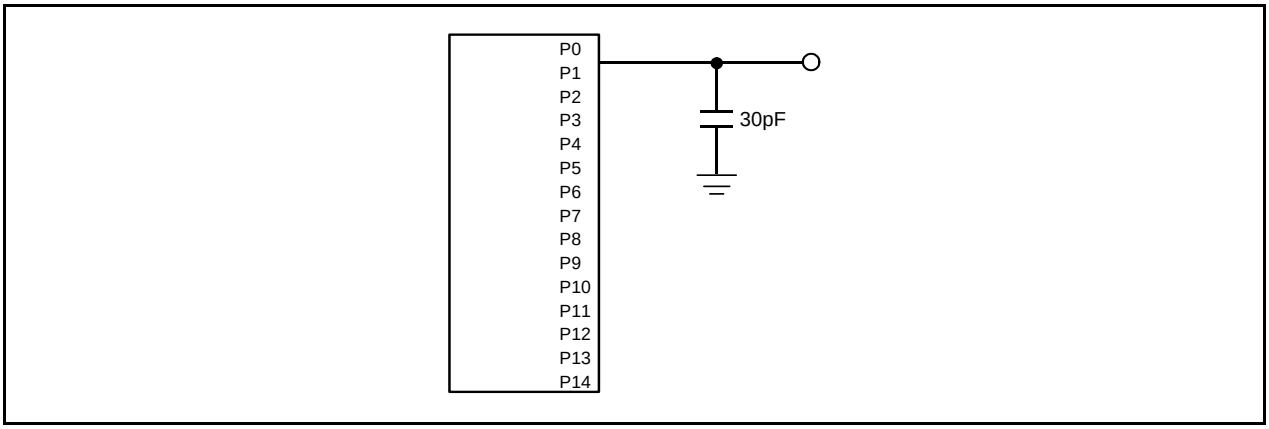


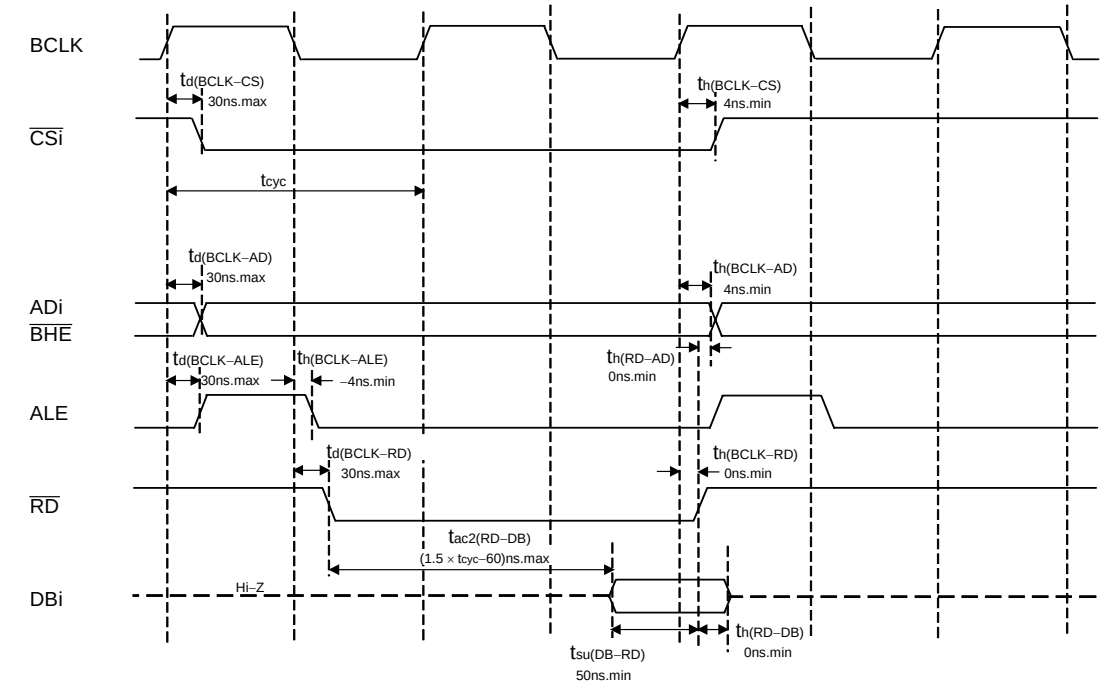
Figure 5.12 Ports P0 to P14 Measurement Circuit

Memory Expansion Mode, Microprocessor Mode

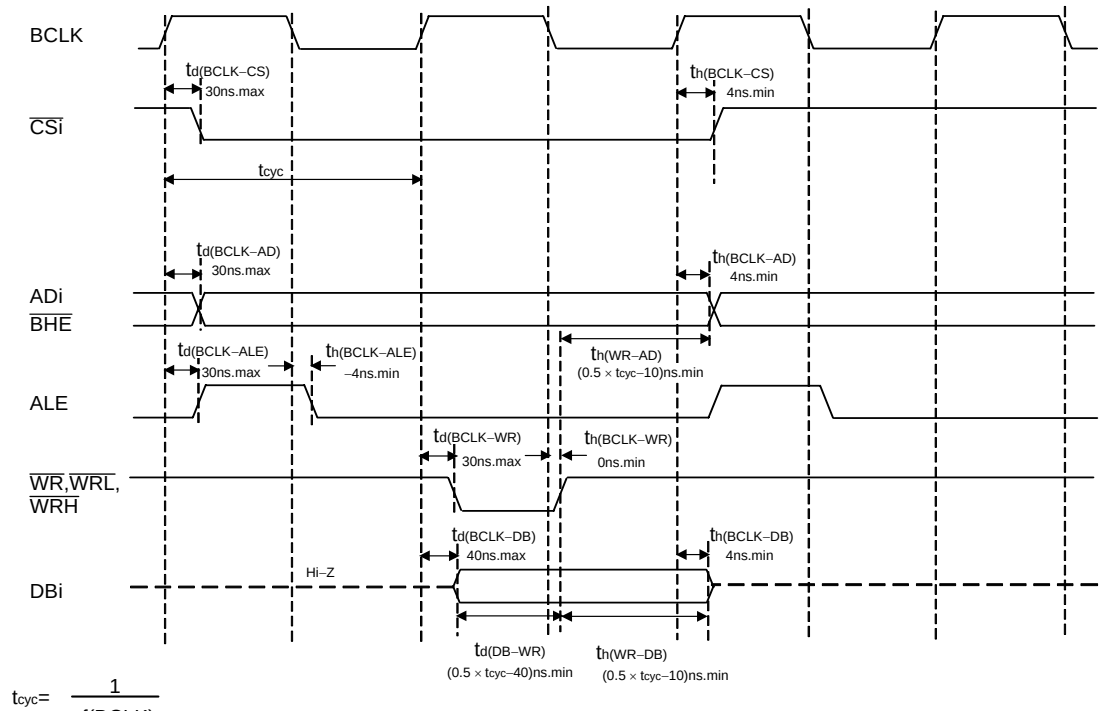
(for 1-wait setting and external area access**)**

$V_{CC1}=V_{CC2}=3V$

Read timing



Write timing



$$t_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions

· $V_{CC1}=V_{CC2}=3V$

· Input timing voltage : $V_{IL}=0.6V$, $V_{IH}=2.4V$

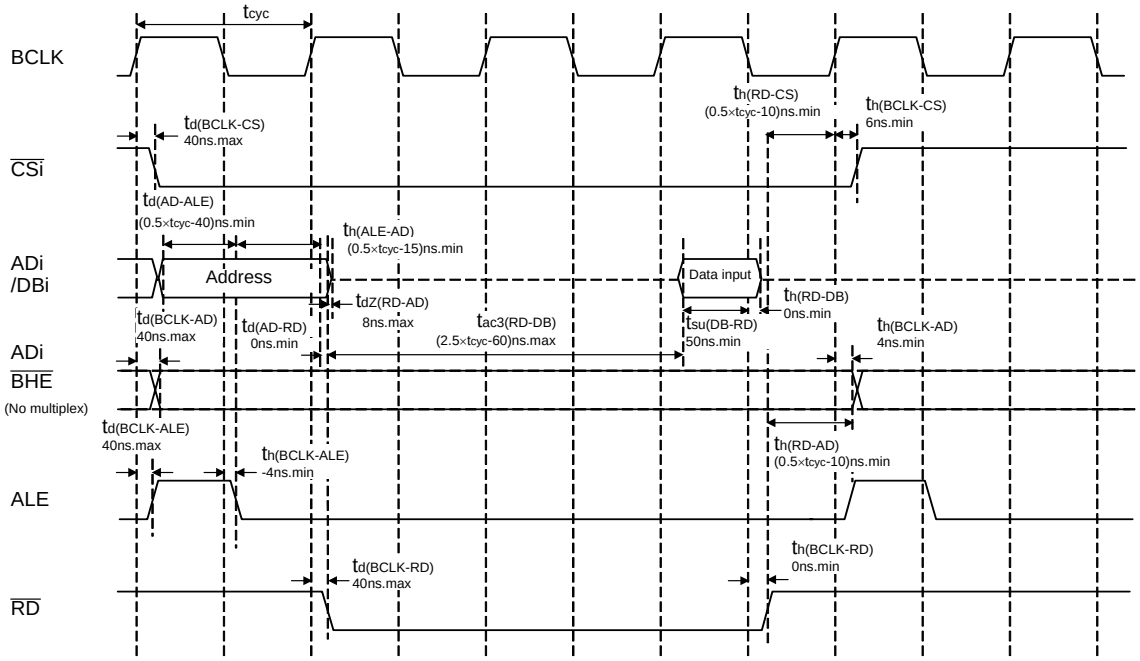
· Output timing voltage : $V_{OL}=1.5V$, $V_{OH}=1.5V$

Figure 5.17 Timing Diagram (5)

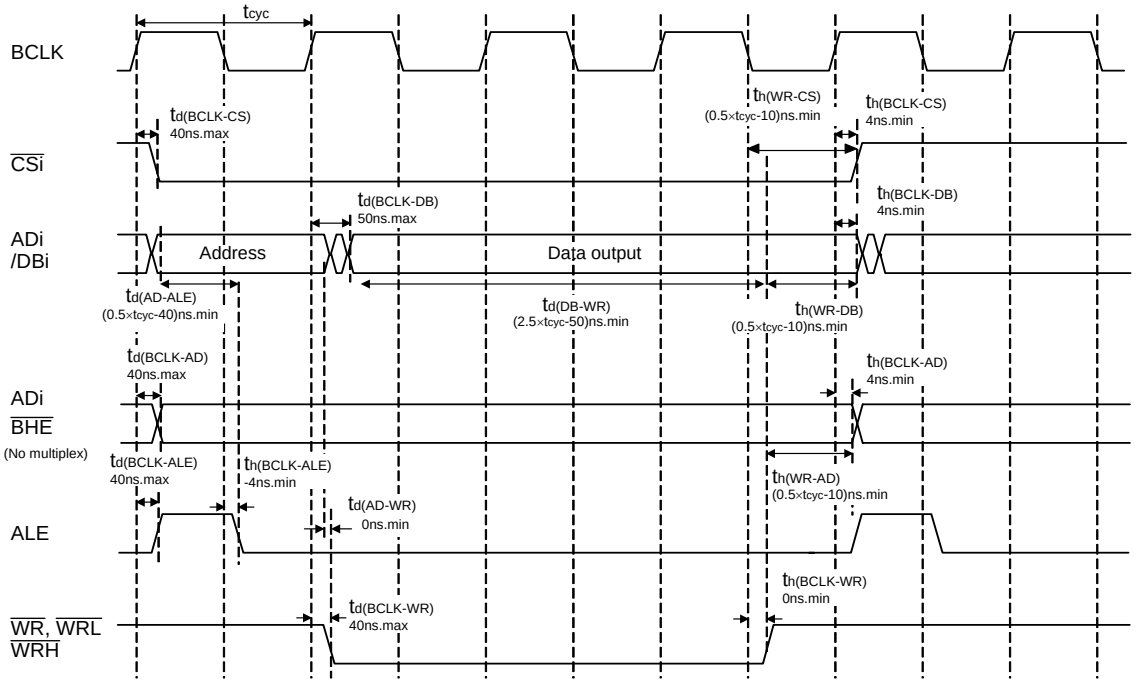
$V_{CC1}=V_{CC2}=3V$

Memory Expansion Mode, Microprocessor Mode
(For 3-wait setting, external area access and multiplex bus selection)

Read timing



Write timing



$$t_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
- $V_{CC1}=V_{CC2}=3V$
- Input timing voltage : $V_{IL}=0.6V$, $V_{IH}=2.4V$
- Output timing voltage : $V_{OL}=1.5V$, $V_{OH}=1.5V$

Figure 5.21 Timing Diagram (9)

5.2 Electrical Characteristics (M16C/62PT)

Table 5.49 Absolute Maximum Ratings

Symbol	Parameter		Condition	Rated Value	Unit
V_{CC1}, V_{CC2}	Supply Voltage		V_{CC1}=V_{CC2}=AVcc	–0.3 to 6.5	V
AVcc	Analog Supply Voltage		V_{CC1}=V_{CC2}=AVcc	–0.3 to 6.5	V
V_I	Input Voltage	$\overline{\text{RESET}}$, CNVSS, BYTE, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, VREF, XIN		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
V_O	Output Voltage	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XOUT		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
P_d	Power Dissipation		–40°C<T_{opr}≤85°C	300	mW
			85°C<T_{opr}≤125°C	200	
T_{opr}	Operating Ambient Temperature	When the Microcomputer is Operating		–40 to 85 / –40 to 125 (2)	°C
		Flash Program Erase		0 to 60	
T_{stg}	Storage Temperature			–65 to 150	°C

NOTES:
1. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.
2. T version = –40 to 85 °C, V version= –40 to 125 °C.

Table 5.53 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (B, U)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

Table 5.54 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (B7, U7) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC}1=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V at T_{opr} = 0 to 60 °C unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Ta (ambient temperature)=55 °C. As to the data hold time except Ta=55 °C, please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor.
6. Referenced to V_{CC1} = 4.5 to 5.5V at T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version)) unless otherwise specified.
7. Table 5.54 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.53.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (B7 and U7).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.55 Flash Memory Version Program/Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(B, U), T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 5.0 V ± 0.5 V	V_{CC1}=4.0 to 5.5 V

$V_{CC1}=V_{CC2}=5V$

Table 5.57 Electrical Characteristics (1) (1)

Symbol	Parameter		Measuring Condition	Standard			Unit
				Min.	Typ.	Max.	
V_{OH}	HIGH Output Voltage (2)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OH}=–5mA	V_{CC1}–2.0		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OH}=–5mA	V_{CC2}–2.0		V_{CC2}	
V_{OH}	HIGH Output Voltage (2)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OH}=–200μA	V_{CC1}–0.3		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OH}=–200μA	V_{CC2}–0.3		V_{CC2}	
V_{OH}	HIGH Output Voltage XOUT	HIGHPOWER	I_{OH}=–1mA	V_{CC1}–2.0		V_{CC1}	V
		LOWPOWER	I_{OH}=–0.5mA	V_{CC1}–2.0		V_{CC1}	
	HIGH Output Voltage XCOUT	HIGHPOWER	With no load applied		2.5		V
		LOWPOWER	With no load applied		1.6		
V_{OL}	LOW Output Voltage (2)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OL}=5mA			2.0	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OL}=5mA			2.0	
V_{OL}	LOW Output Voltage (2)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OL}=200μA			0.45	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OL}=200μA			0.45	
V_{OL}	LOW Output Voltage XOUT	HIGHPOWER	I_{OL}=1mA			2.0	V
		LOWPOWER	I_{OL}=0.5mA			2.0	
	LOW Output Voltage XCOUT	HIGHPOWER	With no load applied		0		V
		LOWPOWER	With no load applied		0		
V_{T+}-V_{T-}	Hysteresis	HOLD, RDY, TA0IN to TA4IN, TB0IN to TB5IN, INT0 to INT5, NMI, ADTRG, CTS0 to CTS2, CLK0 to CLK4, TA0OUT to TA4OUT, KI0 to KI3, RXD0 to RXD2, SCL0 to SCL2, SDA0 to SDA2, SIN3, SIN4		0.2		1.0	V
V_{T+}-V_{T-}	Hysteresis	RESET		0.2		2.5	V
I_{IH}	HIGH Input Current (2)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	V_I=5V			5.0	μA
I_{IL}	LOW Input Current (2)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7,P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	V_I=0V			–5.0	μA
R_{PULLUP}	Pull-Up Resistance (2)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7,P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1	V_I=0V	30	50	170	kΩ
R_{fXIN}	Feedback Resistance XIN				1.5		MΩ
R_{fXCIN}	Feedback Resistance XCIN				15		MΩ
V_{RAM}	RAM Retention Voltage		At stop mode	2.0			V

NOTES:
1. Referenced to $V_{CC1}=V_{CC2}$=4.0 to 5.5V, V_{SS} = 0V at T_{opr} = –40 to 85°C / –40 to 125°C, f(BCLK)=24MHz unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C.
2. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

$V_{CC1}=V_{CC2}=5V$

Timing Requirements
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –40 to 85°C (T version) / –40 to 125°C (V version) unless otherwise specified)

Table 5.59 External Clock Input (XIN input)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	62.5		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	25		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	25		ns
t_r	External Clock Rise Time		15	ns
t_f	External Clock Fall Time		15	ns

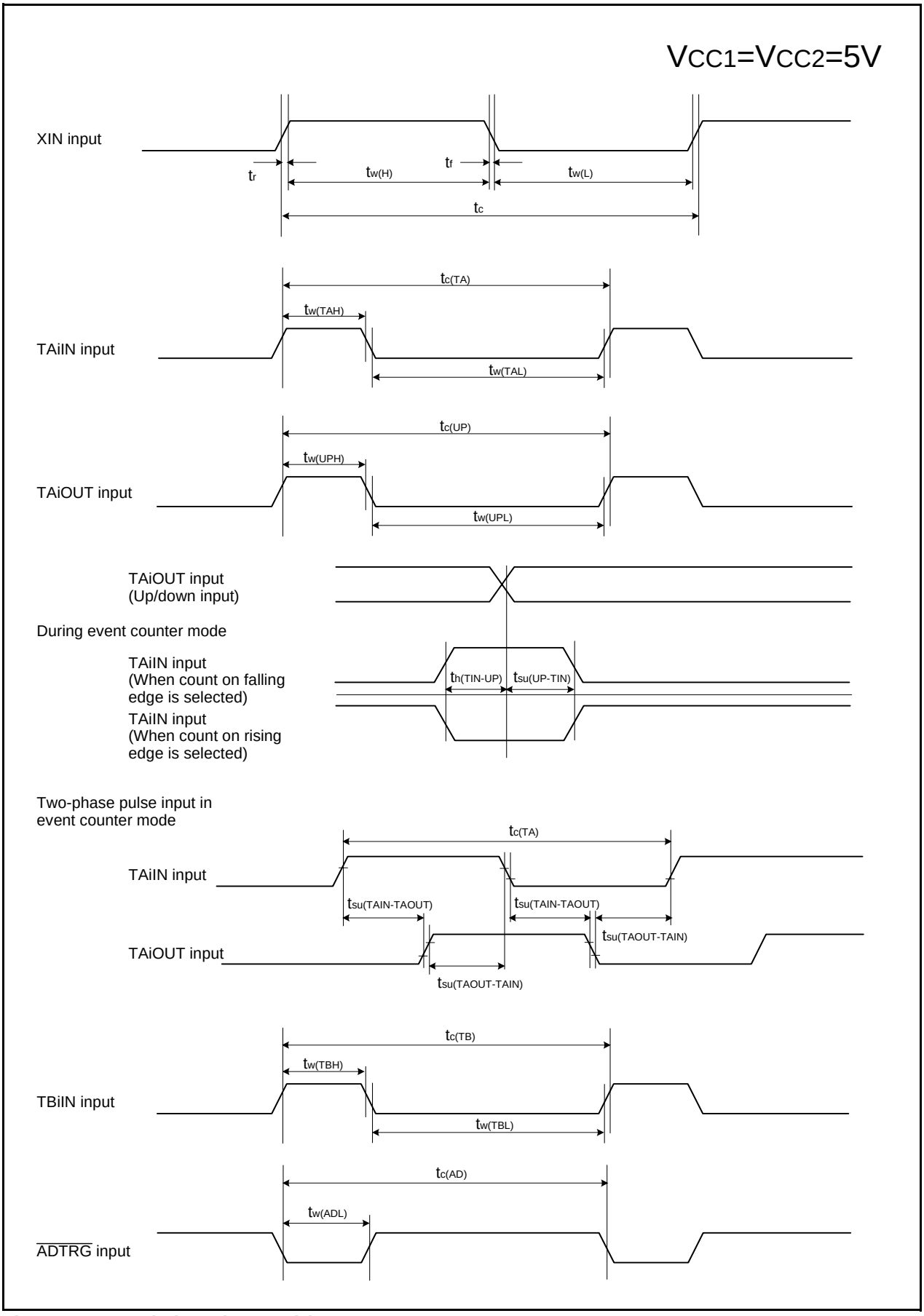


Figure 5.24 Timing Diagram (1)

REVISION HISTORY	M16C/62P Group (M16C/62P, M16C/62PT) Hardware Manual

Rev.	Date	Description	
		Page	Summary
1.10	May 28, 2003	1	Applications are partly revised.
		2	Table 1.1.1 is partly revised.
		4-5	Table 1.1.2 and 1.1.3 is partly revised. "Note 1" is partly revised.
		22	Table 1.5.3 is partly revised.
		23	Table 1.5.5 is partly revised. Table 1.5.6 is added.
		24	Table 1.5.9 is partly revised.
		30	Notes 1 and 2 in Table 1.5.26 is partly revised.
		31	Notes 1 in Table 1.5.27 is partly revised.
		30-31	Note 3 is added to "Data output hold time (refers to BCLK)" in Table 1.5.26 and 1.5.27.
		32	Note 4 is added to "th(ALE-AD)" in Table 1.5.28.
		30-32	Switching Characteristics is partly revised.
		36-39	th(WR-AD) and th(WR-DB) in Figure 1.5.5 to 1.5.8 is partly revised.
		40-41	th(ALE-AD), th(WR-CS), th(WR-DB) and th(WR-AD) in Figure 1.5.9 to 1.5.10 is partly revised.
		42	Note 2 is added to Table 1.5.29.
		47	Notes 1 and 2 in Table 1.5.45 is partly revised.
		48	Notes 1 in Table 1.5.46 is partly revised.
		47-48	Note 3 is added to "Data output hold time (refers to BCLK)" in Table 1.5.45 and 1.5.46.
		49	Note 4 is added to "th(ALE-AD)" in Table 1.5.47.
		47-48	Switching Characteristics is partly revised.
		53-56	th(WR-AD) and th(WR-DB) in Figure 1.5.15 to 1.5.18 is partly revised.
		57-58	th(ALE-AD), th(WR-CS), th(WR-DB) and th(WR-AD) in Figure 1.5.19 to 1.5.20 is partly revised.
2.00	Oct 29, 2003	-	Since high reliability version is added, a group name is revised. M16C/62 Group (M16C/62P) → M16C/62 Group (M16C/62P, M16C/62PT)
		2-4	Table 1.1 to 1.3 are revised. Note 3 is partly revised.
		2-4	Table 1.1 to 1.3 are revised. Note 3 is partly revised.
		6	Figure 1.2 Note5 is deleted.
		7-9	Table 1.4 to 1.7 Product List is partly revised.
		11	Table 1.8 and Figure 1.4 are added.
		12-15	Figure 1.5 to 1.9 ZP is added.
		17,19	Table 1.10 and 1.12 ZP is added to timer A.
		18,20	Table 1.11 and 1.13 VCC1 is added to VREF.
		30	Table 5.1 is revised.
		31-32	Table 5.2 and 5.3 are revised.